

## CLAIMS

1. A resist material comprising one or more surfactants having a fluorine substituent and one or more non-ionic surfactants having neither a fluorine substituent nor a silicon-containing substituent.

2. A resist material according to claim 1 wherein said non-ionic surfactant is one or more compounds selected from the group consisting of polyoxyalkylene alkyl ether esters, polyoxyalkylene alkyl ether, polyoxyalkylene dialkyl ether, polyoxyalkylene aralkyl alkyl ether, polyoxyalkylene aralkyl ether, polyoxyalkylene diaralkyl ether, polyoxyalkylene laurylates.

3. A resist material according to claim 1 being a chemically amplified resist material and subject to exposure to high energy radiation of 500nm or less, X ray or electron beam.

4. A resist material according to claim 2 being a chemically amplified resist material and subject to exposure to high energy radiation of 500nm or less, X ray or electron beam.

5. A pattern formation method comprising a step for coating of a resist material according to claim 1 on a substrate, a step for a subsequent heat treatment, a step for exposure through a photomask to a high energy radiation having wavelength of 500 nm or less, an X ray or an electron

beam, a step for an optional heat treatment, and a step for development in a developing solution.

6. A pattern formation method comprising a step for coating of a resist material according to claim 2 on a substrate, a step for a subsequent heat treatment, a step for exposure through a photomask to a high energy radiation having wavelength of 500 nm or less, an X ray or an electron beam, a step for an optional heat treatment, and a step for development in a developing solution.

7. A pattern formation method comprising a step for coating of a resist material according to claim 3 on a substrate, a step for a subsequent heat treatment, a step for exposure through a photomask to a high energy radiation having wavelength of 500 nm or less, an X ray or an electron beam, a step for an optional heat treatment, and a step for development in a developing solution.

8. A pattern formation method comprising a step for coating of a resist material according to claim 4 on a substrate, a step for a subsequent heat treatment, a step for exposure through a photomask to a high energy radiation having wavelength of 500 nm or less, an X ray or an electron beam, a step for an optional heat treatment, and a step for development in a developing solution.